

MCM68766

Advance Information

8192 × 8-BIT UV ERASABLE PROM

The MC68766 is a 65,536-bit Erasable and Electrically Reprogrammable PROM designed for system debug usage and similar applications requiring nonvolatile memory that could be reprogrammed periodically, or for replacing 64K ROMs for fast turnaround time. The transparent window on the package allows the memory content to be erased with ultraviolet light.

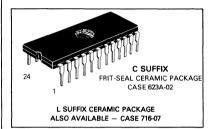
For ease of use, the device operates from a single power supply that has an output enable control and is pin-for-pin compatible with the MCM68366 mask programmable ROMs, which are available for large volume production runs of systems initially using the MCM68766.

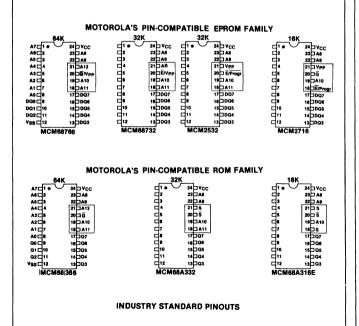
- Single +5 V Power Supply
- Organized as 8192 Bytes of 8 Bits
- Fully TTL Compatible
- Maximum Access Time = 450 ns MCM68766
 350 ns MCM68766-35
- Standard 24-Pin DIP for EPROM Upgradability
- Pin Compatible to MCM68366 Mask Programmable ROM
- Power Dissipation 160 mA Maximum

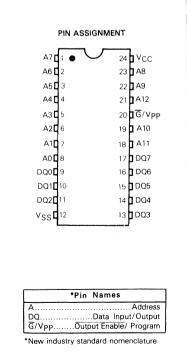
MOS

(N-CHANNEL, SILICON-GATE)

8192×8-BIT UV ERASABLE PROGRAMMABLE READ ONLY MEMORY







ADI843/9-80

ABSOLUTE MAXIMUM RATINGS

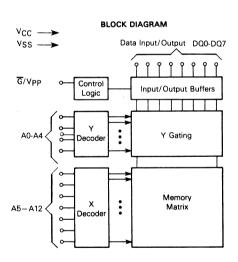
Rating	Value	Unit
Temperature Under Bias	- 10 to +80	°C
Operating Temperature Range	0 to +70	°C
Storage Temperature	-65 to +125	°C
All Input or Output Voltages with Respect to VSS	+6 to -0.3	Vdc
Vpp Supply Voltage with Respect to VSS	+ 28 to -0.3	Vdc

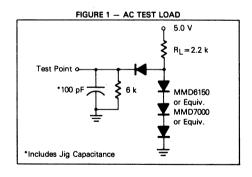
This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit.

NOTE: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPERAT-ING CONDITIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

MODE SELECTION

			Pin I	Number	
Мо	de	9-11, 13-17, DQ	12 VSS	20 G/V _{PP}	24 VCC
Read		Data Out	VSS	VIL	Vcc
Output Disable		High-Z	Vss	VIH	Vcc
Program		Data In	VSS	Pulsed VILP to VIHP	VCC





CAPACITANCE (f = 1.0 MHz, T_A = 25°C, V_{CC} = 5 V periodically sampled rather than 100% tested)

Characteristic	Symbol	Тур	Max	Unit
Input Capacitance (Vin = 0 V) Except G/Vpp	Cin	4.0	6.0	рF
Input Capacitance (G/Vpp)	Cin	60	100	pF
Output Capacitance (V _{Out} = 0 V)	Cout	8.0	12	pF

Capacitance measured with a Boonton Meter or effective capacitance calculated from the lequation: $C = I\Delta_t/\Delta V$.

DC OPERATING CONDITIONS AND CHARACTERISTICS

(Full operating voltage and temperature range unless otherwise noted)

RECOMMENDED DC OPERATING CONDITIONS

Pa	rameter	Symbol	Min	Nom	Max	Unit
Supply Voltage	MCM68766 MCM68766-35	Vcc	4.75 4.5	5.0 5.0	5.25 5.5	Vdc
Input High Voltage	Wildings 33	VIH	2.0	-	V _{CC} + 1.0	Vdc
Input Low Voltage		VIL	-0.1		0.8	Vdc

DC OPERATING CHARACTERISTICS

Characteristic	Condition	Symbol	Min	Тур	Max	Units
Address Input Sink Current	$V_{in} = 5.25 \text{ V}$	lin	_	_	10	μΑ
Output Leakage Current	$V_{out} = 5.25 \text{ V}$	lLO	_	_	10	μΑ
G/Vpp Input Sink Current	$\overline{G}/Vpp = 0.4 V$	lGL	-	-	100	μΑ
	$\overline{G}/V_{PP} = 2.4 V$	IGH = IPL	-	_	400	μΑ
V _{CC} Supply Current (Outputs Open)	$\overline{G}/V_{PP} = V_{IL}$	Icc	1	-	160	mΑ
Output Low Voltage	$I_{OL} = 2.1 \text{ mA}$	VOL	-	_	0.45	٧
Output High Voltage	$I_{OH} = -400 \mu A$	۷он	2.4	_	-	V

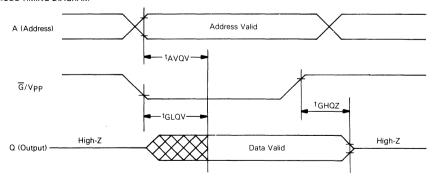
AC OPERATING CONDITIONS AND CHARACTERISTICS

(Full operating voltage and temperature range unless otherwise noted)

Input Bules Louise	Input Timing Levels	1.0 Volt and 2 Volts
Input Pulse Levels		0.8 Volt and 2 Volts
Input Rise and Fall Times20 r	Output Load	See Figure 1

Characteristic Address Valid to Output Valid G to Output Valid G to Hi-Z Output	0 412		MCM68766- 35		MCM68766		
Characteristic	Condition	Symbol	Min	Max	Min	Max	Units
Address Valid to Output Valid	$\overline{G} = V_{1L}$	tAVQV	_	350		450	ns
G to Output Valid		¹ GLQV	-	150	-	150	ns
G to Hi-Z Output	_	tGHQZ	0	100	0	100	ns
Data Hold from Address	$\overline{G} = V_{IL}$	tAXDX	0		0	_	ns

READ MODE TIMING DIAGRAM



DC PROGRAMMING CONDITIONS AND CHARACTERISTICS

 $(T_A = 25 \pm 5^{\circ}C)$

RECOMMENDED PROGRAMMING OPERATING CONDITIONS

Parameter	Symbol	Min	Nom	Max	Unit
Supply Voltage	Vcc	4.75	5.0	5.25	Vdc
Input High Voltage for All Addresses and Data	VIH	2.2	_	V _{CC} + 1	Vdc
Input Low Voltage for All Addresses and Data	VIL	-0.1	1	0.8	Vdc
Program Pulse Input High Voltage	VIHP	24	25	26	Vdc
Program Pulse Input Low Voltage	VILP	2.0	Vcc	6.0	Vdc

PROGRAMMING OPERATION DC CHARACTERISTICS

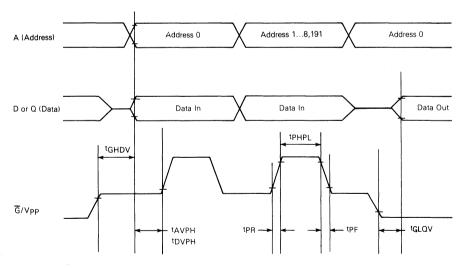
Characteristic	Condition	Symbol	Min	Тур	Max	Unit
Address Input Sink Current	$V_{in} = 5.25 V$	ILI	_	-	10	μAdc
Vpp Program Pulse Supply Current (Vpp = 25 V ± 1 V)	_	IРН	-	-	30	mAdc
Vpp Supply Current (Vpp=2.4 V)	_	IPL = IGH	_	-	400	μΑ
VCC Supply Current (Vpp=5 V)	_	¹ CC	_	-	160	mAdc

AC PROGRAMMING OPERATING CONDITIONS AND CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit
Address Setup Time	[†] AVPH	2.0	_	μS
Data Setup Time	^t DVPH	2.0	_	μS
Output Enable to Valid Data	tGLQV	150	-	ns
Output Disable to Data In	tGHDV	2.0	-	μS
Program Pulse Width	^t PHPL	1.9	2.1	ms
Program Pulse Rise Time	tPR	0.5	2.0	μS
Program Pulse Fall Time	tpF	0.5	2.0	μS
Cumulative Programming Time Per Word*	tCP	12	50	ms

^{*}Block mode programming must be used. Block mode programming is defined as one program pulse applied to each of the 8,192 address locations in sequence. Multiple blocks are used to accumulate programming time (tcp).

PROGRAMMING OPERATION TIMING DIAGRAM



PROGRAMMING INSTRUCTIONS

After the completion of an ERASE operation, every bit in the device is in the "1" state (represented by Output High). Data are entered by programming zeros (Output Low) into the required bits. The words are addressed the same way as in the READ operation. A programmed "0" can only be changed to a "1" by ultraviolet light erasure.

To set the memory up for Program Mode, the \overline{G}/Vpp input (Pin 20) should be between +2.0 and +6.0 V, which will three-state the outputs and allow data to be set up on the DQ terminals. The V_{CC} voltage is the same as for the Read operation. Only "0's" will be programmed when "0's" and "1's" are entered in the 8-bit data word.

After address and data setup, 25-volt programming pulse $(V_{|H} \ to \ V_{|HP})$ is applied to the G/Vpp input. The program pulse width is 2 ms and the maximum program pulse amplitude is 26 V.

Multiple MCM68766s may be programmed in parallel by connecting like inputs and applying the program pulse to the \overline{G}/Vpp inputs. Different data may be programmed into multiple MCM68766s connected in parallel by selectively applying the programming pulse only to the MCM68766s to be programmed.

READ OPERATION

After access time, data is valid at the outputs in the Read mode. With $\overline{G}/Vpp="0"$ the outputs are enabled; with $\overline{G}/Vpp="1"$ the outputs are three-stated.

Multiple MCM68766s may share a common data bus with like outputs OR-tied together. In this configuration only one \overline{G}/Vpp input should be low and no other device outputs should be active on the same bus. This will prevent data contention on the bus.

ERASING INSRUCTIONS

The MCM68766 can be erased by exposure to high intensity shortwave ultraviolet light, with a wavelength of 2537 angstroms. The recommended integrated dose (i.e., UV-intensity X exposure time) is 15 Ws/cm². As an example, using the "Model 30-000" UV Eraser (Turner Designs, Mountain View, CA 94043) the ERASE-time is 36 minutes. The lamps should be used without shortwave filters and the MCM68766 should be positioned about one inch away from the UV-tubes.